



STQ1NE10L

N-CHANNEL 100V - 0.3 Ω - 1A TO-92 STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STQ1NE10L	100 V	<0.4 Ω	1 A

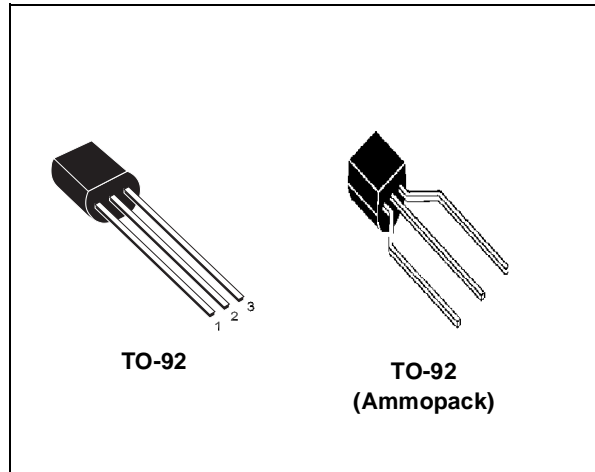
- TYPICAL R_{DS(on)} = 0.3 Ω
- EXCEPTIONAL HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- AVALANCHE RUGGED TECHNOLOGY
- LOW THRESHOLD DRIVE

DESCRIPTION

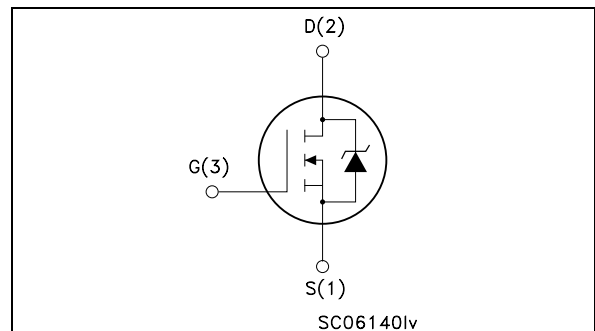
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC MOTOR CONTROL (DISK DRIVES, etc.)
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	100	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C	1	A
I _D	Drain Current (continuous) at T _C = 100°C	0.6	A
I _{DM} (●)	Drain Current (pulsed)	4	A
P _{tot} (1)	Total Dissipation at T _C = 25°C	3	W
	Derating Factor	0.025	W/°C
dv/dt (2)	Peak Diode Recovery voltage slope	6	V/ns
EAS (3)	Single Pulse Avalanche Energy	400	mJ
T _{stg}	Storage Temperature	-55 to 150	°C
T _j	Operating Junction Temperature		°C

(●) Pulse width limited by safe operating area.

(1) Related to R_{thj -1}

(2) I_{SD} ≤ 1A, di/dt ≤ 200A/μs, V_{DD} ≤ V(BR)DSS, T_j ≤ T_{JMAX}

(3) Starting T_j = 25 °C, I_D = 1A, V_{DD} = 50V

STQ1NE10L

THERMAL DATA

Rthj-Lead	Thermal Resistance Junction-Lead	Max	40	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	125	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	Typ	260	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1		2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 0.5 A V _{GS} = 5 V I _D = 0.5 A		0.30 0.35	0.40 0.45	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15V I _D = 0.5 A		2		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		345 45 20		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 50\text{ V}$ $I_D = 0.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		11 12		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 1\text{ A}$ $V_{GS} = 5\text{ V}$		7 1.5 3.5		nC nC nC

SWITCHING OFF

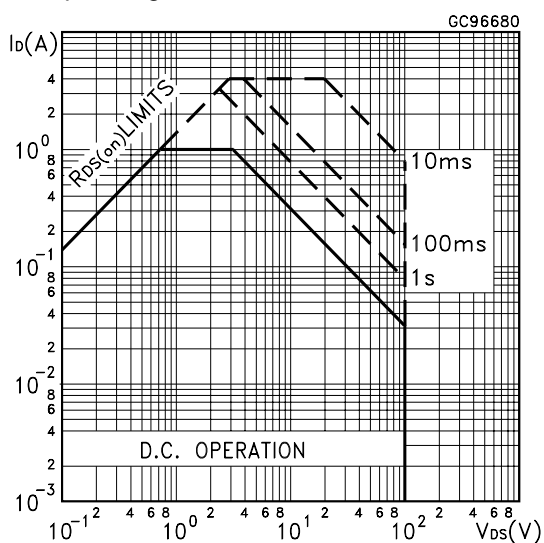
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 50\text{ V}$ $I_D = 0.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 5\text{ V}$ (Resistive Load, Figure 3)		20 13		ns ns

SOURCE DRAIN DIODE

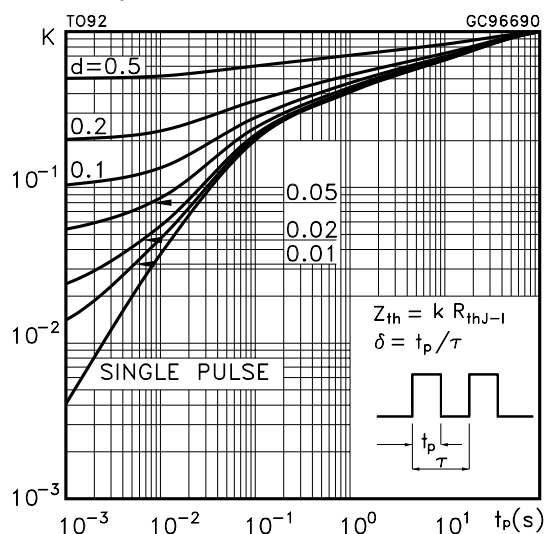
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				1 4	A A
$V_{SD} (^*)$	Forward On Voltage	$I_{SD} = 1\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 1\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		52 90 3.5		ns nC A

(*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 (•)Pulse width limited by safe operating area.

Safe Operating Area

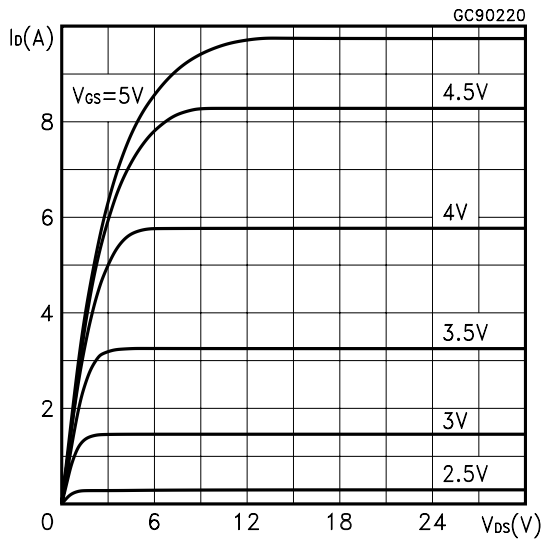


Thermal Impedance Junction-lead

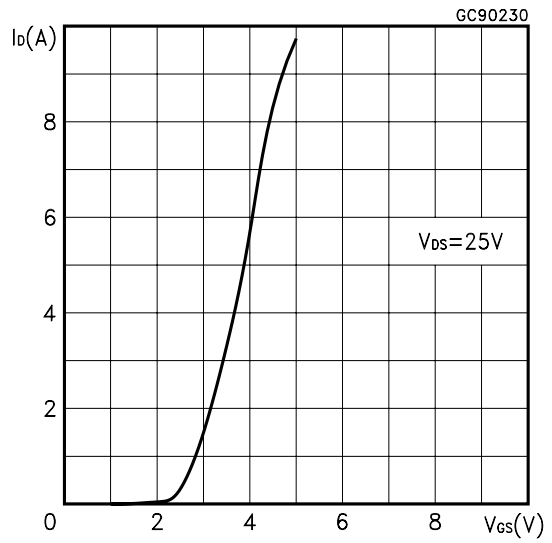


STQ1NE10L

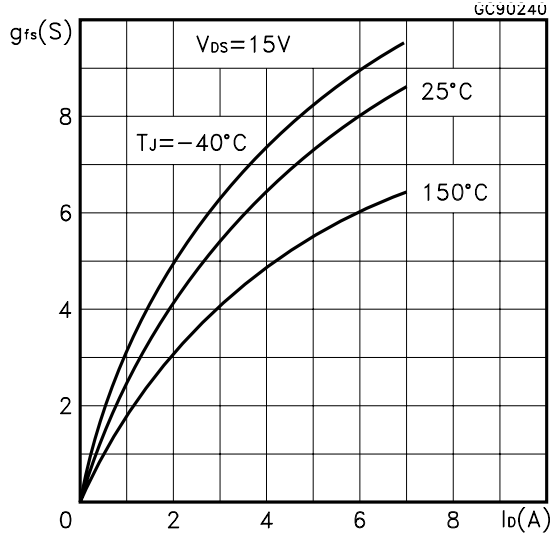
Output Characteristics



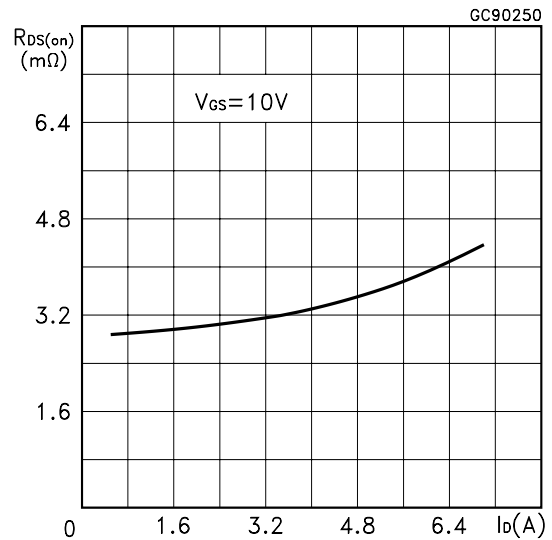
Transfer Characteristics



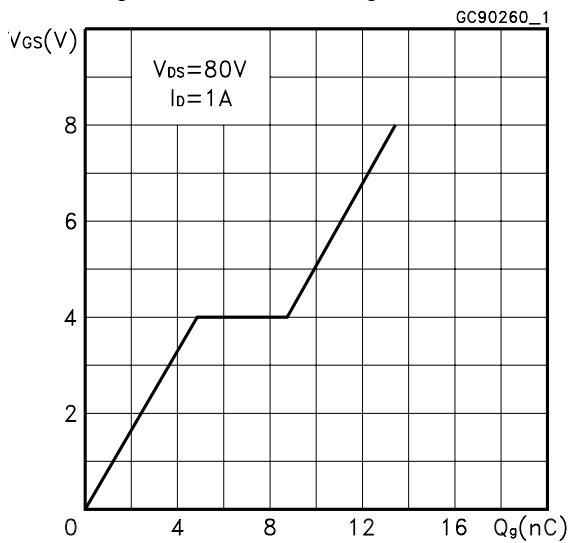
Transconductance



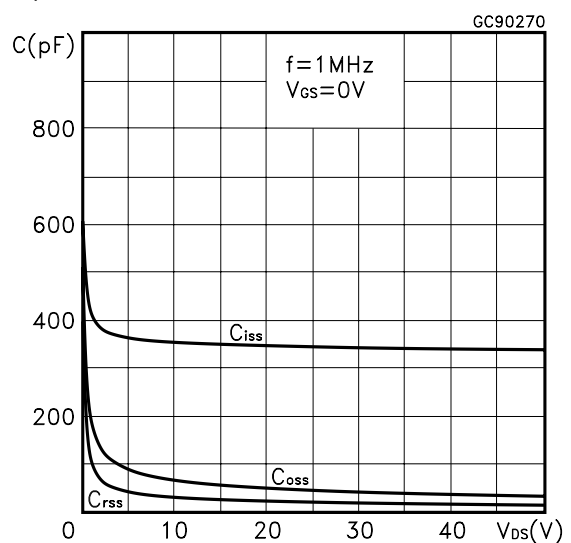
Static Drain-source On Resistance



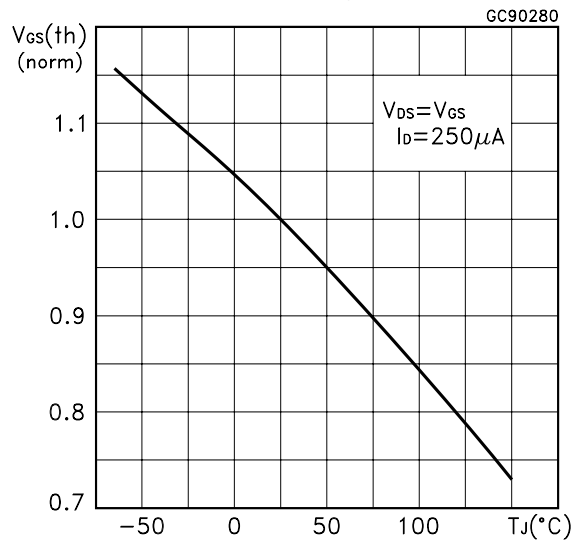
Gate Charge vs Gate-source Voltage



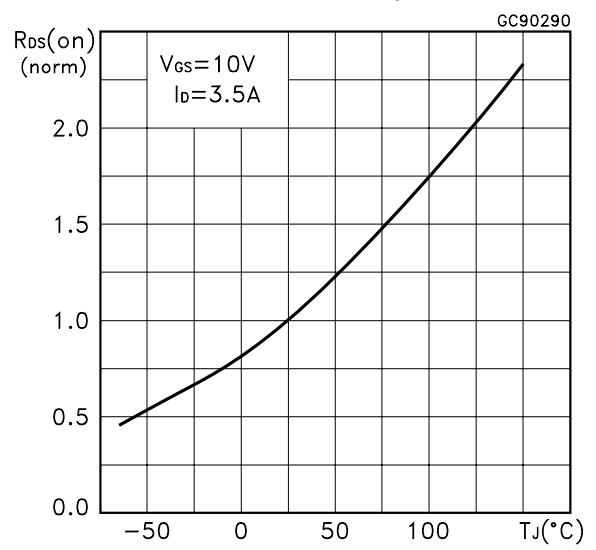
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics

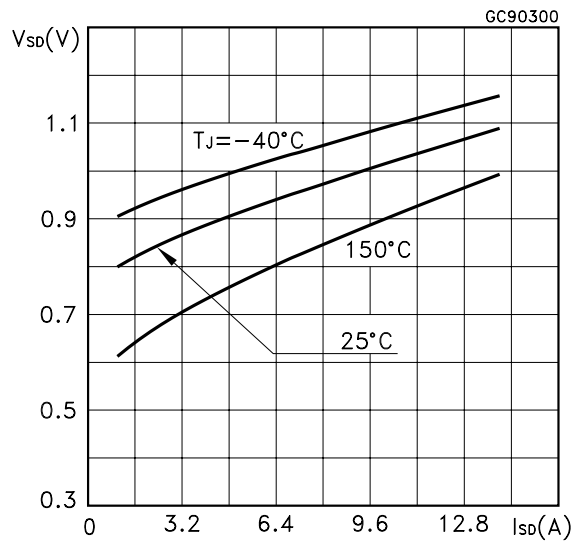


Fig. 1: Unclamped Inductive Load Test Circuit

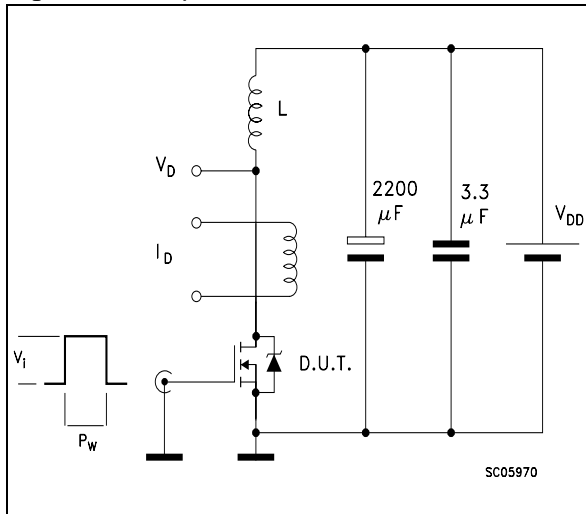


Fig. 2: Unclamped Inductive Waveform

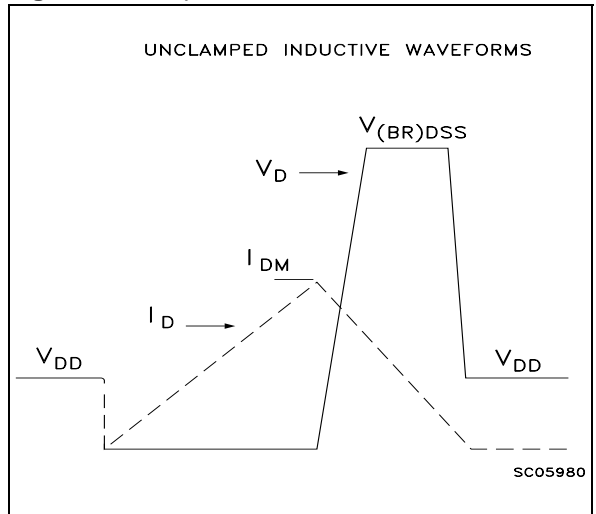


Fig. 3: Switching Times Test Circuits For Resistive Load

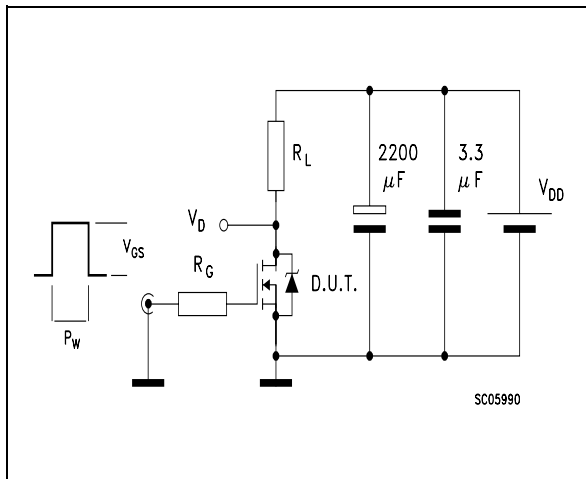


Fig. 4: Gate Charge test Circuit

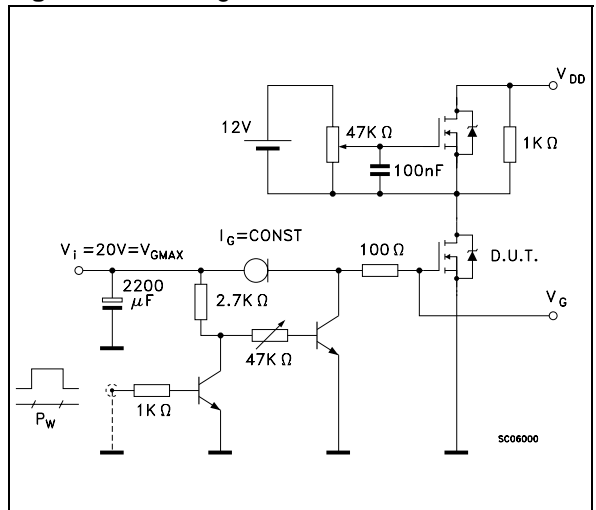
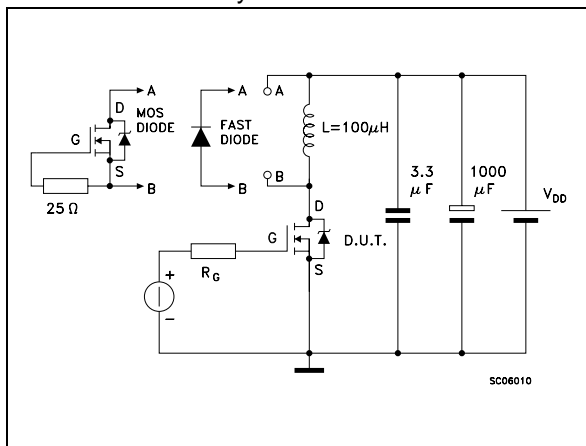
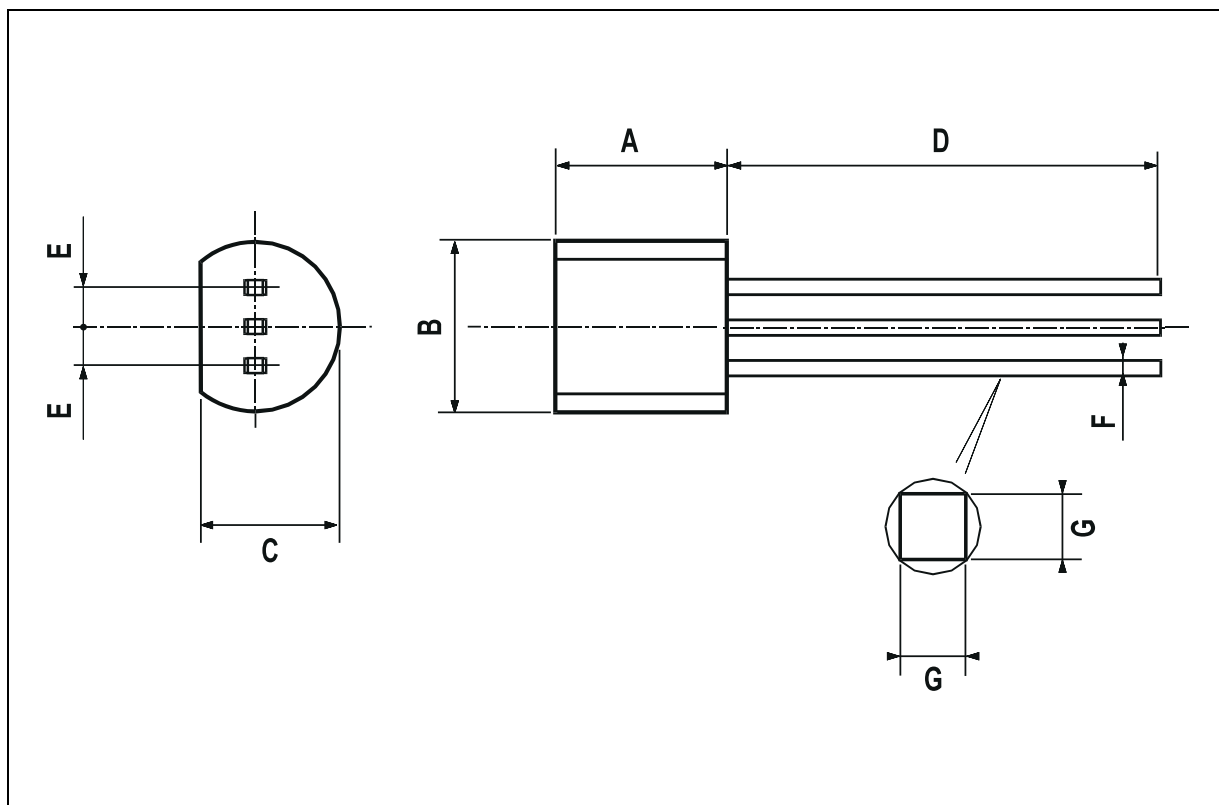


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



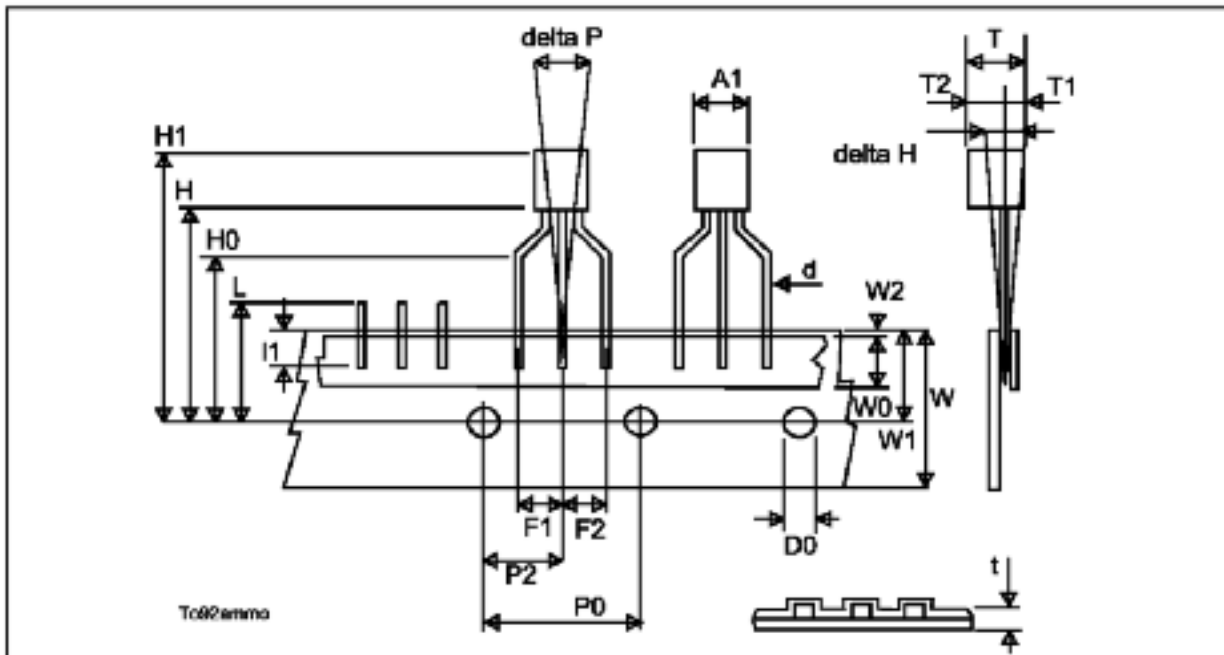
TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.58		5.33	0.180		0.210
B	4.45		5.2	0.175		0.204
C	3.2		4.2	0.126		0.165
D	12.7			0.500		
E		1.27			0.050	
F	0.4		0.51	0.016		0.020
G	0.35			0.14		



TO-92 AMMOPACK

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A1			4.8			0.19
T			3.8			0.15
T1			1.6			0.06
T2			2.3			0.09
d			0.48			0.02
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
l1	3			0.11		
delta P	-1		1	-0.04		0.04



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics
© 2002 STMicroelectronics - All Rights Reserved

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco -
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>